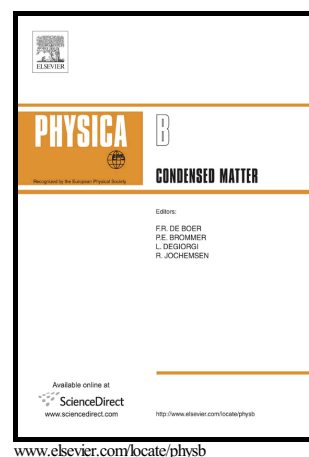


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Investigation of effect of annealing on thermally evaporated ZnSe thin films through spectroscopic techniques

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Abstract

ZnSe thin films have been grown on clean glass substrates by thermal evaporation technique and deposited films have been annealed at 473K. William-Hall method has been adopted to extract information on crystallite size and internal strain in the film from X-ray diffractogram. Effect of annealing on ZnSe films has been analyzed by spectroscopic techniques which include optical absorption, Raman, and photoluminescence spectroscopy. From optical absorption, band gap has been estimated along with other optical parameters like refractive index and extinction coefficient. Also, Urbach tail, which originates near band edge due to structural disorders, has been characterized. Raman spectra have been analyzed to get the information on the influence of crystallite size and strain effect on peak position, intensity and width. Photoluminescence spectra have been recorded and analyzed to get an insight on defect levels induced due to vacancies, interstitials, and impurity complexes.

Keywords: II – VI compound semiconductors; Raman spectroscopy; Photoluminescence; PVD; W – H plot; Solar cell materials.

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